

Atty Docket No.: JCLA8894

Serial No.: 10/084,761

*A2*  
*B1*

3. (Once Amended) A substrate cutting method as set forth in Claim 1, characterized in that a surface layer of the substrate is irradiated with said laser.

*A3*  
*B1*

11. (Once Amended) A substrate cutting method as set forth in Claim 10, characterized in that the thickness of said semiconductor wafer is equal to or less than 50  $\mu$ m.